



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re U.S. Patent application:)
Hisato SHINOHARA et al.)
Application Serial No. 08/169,127) Art Unit: 1762
Filed: December 20, 1993) Examiner: Marianne L. Padgett
For: METHOD AND SYSTEM OF)
LASER PROCESSING)

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SECOND SUPPLEMENTAL AMENDMENT

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TC 1700

Commissioner for Patents
Washington, D.C. 20231

Sir:

In further response to the Office Action mailed July 30, 2002 and the Examiner's interview of October 10, 2002, please amend the above-identified application as follows:

IN THE TITLE:

Please replace the Title with the following:

--LASER IRRADIATION METHOD--

IN THE SPECIFICATION:

Please amend the specification as follows:

Page 10, fourth full paragraph continuing onto page 11:

As shown in Fig. 7(A), a non-single crystalline semiconductor film 52 such as an amorphous silicon or solid phase crystallized silicon is formed by plasma CVD on a soda-lime glass substrate 1 having a silicon oxide or silicon nitride blocking layer 51 having a thickness of 1000-4000Å, e.g. 2000 Å on its surface. The non-single crystalline semiconductor layer 52 is substantially intrinsic but a suitable dopant species such as boron or arsenic may be added therein. Optionally, hydrogen or a halogen such as fluorine may be added to the semiconductor layer 52 as a dangling bond neutralizer. Also, the semiconductor layer 52 is 200-1500Å thick, for

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02 FC:1202

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